

## CLAIMS

1. A hot plate for a semiconductor producing/examining device,  
comprising a resistance heating element formed on a surface of  
5 a ceramic substrate or inside the ceramic substrate,  
wherein the glossiness of the heating face of said ceramic  
substrate is 1.5 % or more.

10 2. The hot plate for a semiconductor producing/examining  
device according to claim 1,  
wherein said ceramic substrate contains 0.5 to 10 weight %  
of oxygen.

15 3. The hot plate for a semiconductor producing/examining  
device according to claim 1 or 2,  
wherein said ceramic substrate is subjected to an annealing  
treatment.

20 4. The hot plate for a semiconductor producing/examining  
device according to any of claims 1 to 3,  
wherein said ceramic substrate is subjected to a cold  
isostatic pressing process before it is sintered.

Sub  
A2  
Add A3